

ABSTRACT OF THE DISCLOSURE

The present invention provides a channel region of a depletion
5 type lateral field effect transistor. The channel region of a first conductivity
type is selectively provided in a semiconductor region of a second
conductivity type, and the channel region underlies a gate insulating film,
wherein an interface of the channel region to the gate insulating film lies at
a lower level than an upper surface of the semiconductor region.

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